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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re application of: Hill et al.

Attorney Docket No.:  
NOVLP050D1/NVLS-000682D1

Application No.: NEW

Examiner: UNASSIGNED

Filed: HEREWITH

Group: UNASSIGNED

Title: METHOD OF FABRICATING LOW  
DIELECTRIC CONSTANT DIELECTRIC  
FILMS

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**INFORMATION DISCLOSURE STATEMENT**  
**37 CFR §§1.56 AND 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

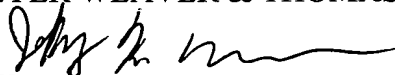
The references listed in the attached PTO Form 1449 may be material to examination of the above-identified patent application. Applicants submit the list of these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application. The above-identified application is a Divisional of prior application U.S. Patent Application No. 10/171,289. This prior application is being relied upon for an earlier filing date under 35 U.S.C. § 120. Because the listed references were either cited by the PTO, or submitted to the PTO in the prior application, under 37 CFR § 1.98(d) Applicants submit that copies need not be provided.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP050D1).

Respectfully submitted,

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<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. NOVLP050D1/NVLS- 000682D1 Applicant: Hill et al. Filing Date HEREWITH	Application No.: NEW  Group UNASSIGNED

**U.S. Patent and Published Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,329,062	12/11/01	Gaynor			
	A2	6,268,276	7/31/01	Chan et al.			
	A3	6,177,329	1/23/01	Pang			
	A4	5,920,790	07/99	Wetzel et al.			
	A5	2003/0119307	06/03	Bekiaris et al.			

**Foreign Patent or Published Foreign Patent Application**

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1	WO95/07543	03/16/95	WIPO			X	

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	R.D. Miller et al., "Phase-Separated Inorganic-Organic Hybrids for Microelectronic Applications," MRS Bulletin, October 1997, Pages 44-48
	C2	Jin et al., "Nanoporous Silica as an Ultralow- $\kappa$ Dielectric," MRS Bulletin, October 1997, Pages 39-42
	C3	Cleemput et al., "Dielectric Films With Low Dielectric Constants," Application Serial No.: 09/727,796, filed November 30, 2000,
	C4	Asoh et al., "Fabrication of Ideally Ordered Anodic Porous Alumina with 63 nm Hole Periodicity Using Sulfuric Acid," J. Vac. Sci. Technol. B 19(2), Mar/Apr 2001, Pages 569-572
	C5	Asoh et al., "Conditions for Fabrication of Ideally Ordered Anodic Porous Alumina Using Pretextured Al," Journal of the Electrochemical Society, 148 (4) B152-B156 (2001) Pages B152-B156
	C6	Holland et al., "Nonlithographic Technique for the Production of Large Area High Density Gridded Field Sources," J. Vac. Sci. Technol. B 17(2), Mar/Apr. 1999, Pages 580-582
	C7	Masuda et al. "Highly Ordered Nanochannel-Array Architecture in Anodic Alumina," App. Phys. Lett. 71(19), November 1997, Pages 2770-2772

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	Applicant: Hill et al. Filing Date HEREWITH	Group UNASSIGNED

	C8	Clube et al., "White Paper from Holotronic Technologies SA; downloaded from <a href="http://www.hdotronic.com/whitepaper/fine-patt.pdf">www.hdotronic.com/whitepaper/fine-patt.pdf</a> on March 12, 2002
	C9	Meli et al., "Self-Assembled Masks for the Transfer of Nanometer-Scale Patterns into Surfaces: Characterization by AFM and LFM", Nano Letters, Vol. 2, No. 2, 2002, 131-135
	C10	"Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003.
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.